

NPN SILICON TRANSISTOR

Qualified per MIL-PRF-19500/727

DEVICES

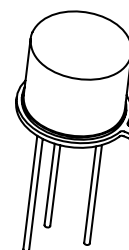
2N5010	2N5013	2N5010S	2N5013S
2N5011	2N5014	2N5011S	2N5014S
2N5012	2N5015	2N5012S	2N5015S

LEVELS

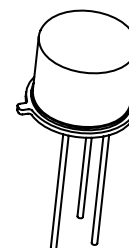
JAN
JANTX
JANTXV

ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ\text{C}$ unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	500	Vdc
		600	Vdc
		700	Vdc
		800	Vdc
		900	Vdc
		1000	Vdc
Collector-Base Voltage	V_{CBO}	500	Vdc
		600	Vdc
		700	Vdc
		800	Vdc
		900	Vdc
		1000	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current	I_{C}	200	mAdc
Base Current	I_{B}	20	mAdc
Total Power Dissipation	P_{t}	1.0	W
		7.0	W
Thermal Resistance, Junction to Case 1/	$R_{\theta\text{JC}}$	20	$^\circ\text{C/W}$
Operating & Storage Junction Temperature Range	$T_{\text{j}}, T_{\text{stg}}$	-65 to +200	$^\circ\text{C}$



TO-5
2N5010 thru 2N5015



TO-39
2N5010S thru 2N5015S

Note:

1/ See 19500/727 for Thermal Derating Curves.

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Collector to Base Cutoff Current $V_{CB} = 400\text{V}$ 2N5010 $V_{CB} = 500\text{V}$ 2N5011 $V_{CB} = 580\text{V}$ 2N5012 $V_{CB} = 650\text{V}$ 2N5013 $V_{CB} = 700\text{V}$ 2N5014 $V_{CB} = 760\text{V}$ 2N5015	I_{CBO1}		10 10 10 10 10 10	nAdc nAdc nAdc nAdc nAdc nAdc
@ $T_A = +150^\circ\text{C}$ $V_{CB} = 400\text{V}$ 2N5010 $V_{CB} = 500\text{V}$ 2N5011 $V_{CB} = 588\text{V}$ 2N5012 $V_{CB} = 650\text{V}$ 2N5013 $V_{CB} = 700\text{V}$ 2N5014 $V_{CB} = 760\text{V}$ 2N5015	I_{CBO2}		10 10 10 10 10 10	uAdc uAdc uAdc uAdc uAdc uAdc
Emitter to Base Cutoff Current $V_{EB} = 4\text{V}$	I_{EBO}		20	uAdc
Collector to Base Breakdown Voltage $I_C = 0.1\text{mAdc}$ 2N5010 $I_C = 0.1\text{mAdc}$ 2N5011 $I_C = 0.1\text{mAdc}$ 2N5012 $I_C = 0.2\text{mAdc}$ 2N5013 $I_C = 0.2\text{mAdc}$ 2N5014 $I_C = 0.2\text{mAdc}$ 2N5015	$V_{(BR)CBO}$	500 600 700 800 900 1000		Vdc Vdc Vdc Vdc Vdc Vdc
Emitter to Base Breakdown Voltage $I_C = 0\text{mA}$ $I_E = 0.05\text{mA}$	$V_{(BR)EBO}$	5		Vdc
Collector to Emitter Breakdown Voltage $R_{BE} = 1\text{K}\Omega$ 2N5010 $I_C = 0.2\text{mA}$, Pulsed 2N5011 2N5012 2N5013 2N5014 2N5015	$V_{(BR)CER}$	500 600 700 800 900 1000		Vdc Vdc Vdc Vdc Vdc Vdc
Forward-Current Transfer Ratio $I_C = 25\text{mA}$ 2N5010, 2N5011, 2N5012 $I_C = 20\text{mA}$ 2N5013, 2N5014, 2N5015 $V_{CE} = 10\text{V}$	h_{FE1}	30 30	180 180	
$V_{CE} = 10\text{V}$ $I_C = 5\text{mA}$	h_{FE2}	10		
$V_{CE} = 10\text{V}$ $I_C = 20\text{mA}$ @ $T_A = -55^\circ\text{C}$	h_{FE3}	10		

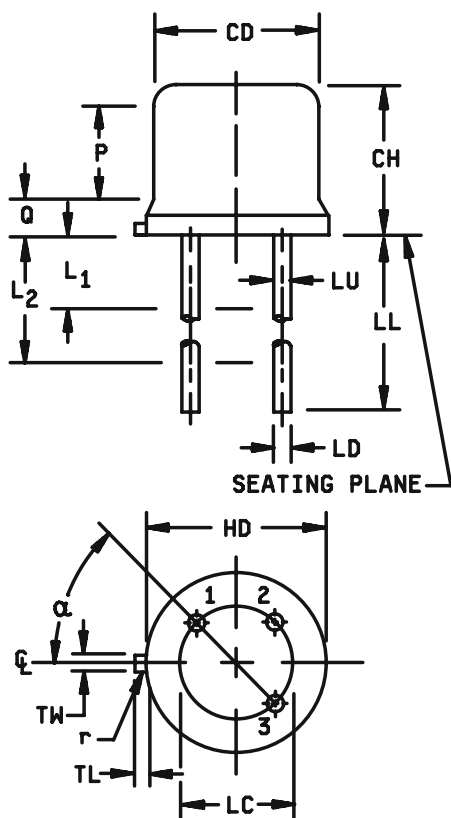
ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted) (Cont.)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Base-Emitter Saturation Voltage $I_C = 25\text{mA}$ 2N5010, 2N5011, 2N5012 $I_C = 20\text{mA}$ 2N5013, 2N5014, 2N5015 $I_B = 5\text{mA}$, Pulsed	$V_{BE(SAT)}$		1.0 1.0	Vdc Vdc
Collector-Emitter Saturation Voltage $I_C = 25\text{mA}$ 2N5010 $I_C = 25\text{mA}$ 2N5011 $I_C = 25\text{mA}$ 2N5012 $I_C = 20\text{mA}$ 2N5013 $I_C = 20\text{mA}$ 2N5014 $I_C = 20\text{mA}$ 2N5015 $I_B = 5\text{mA}$, Pulsed	$V_{CE(SAT)}$		1.4 1.5 1.6 1.6 1.6 1.8	Vdc Vdc Vdc Vdc Vdc Vdc

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Magnitude of small signal short-circuit forward current transfer ratio $V_{CE} = 10\text{Vdc}$, $I_C = 25\text{mA}$, $f = 10\text{MHz}$ 2N5010, 2N5011, 2N5012 $V_{CE} = 10\text{Vdc}$, $I_C = 20\text{mA}$, $f = 10\text{MHz}$ 2N5013, 2N5014, 2N5015	$ h_{fe} $	1.0 1.0		
Open circuit output capacitance $V_{CB} = 10\text{V}$, $I_E = 0$, $f = 2\text{MHz}$	C_{obo}		30	pF

PACKAGE DIMENSIONS



	Dimensions				
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	6
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TP		5.08 TP		7
LD	.016	.019	0.41	0.48	8,9
LL	See note 14				
LU	.016	.019	0.41	0.48	8,9
L ₁		.050		1.27	8,9
L ₂	.250		6.35		8,9
P	.100		2.54		7
Q		.030		0.76	5
TL	.029	.045	0.74	1.14	3,4
TW	.028	.034	0.71	0.86	3
r		.010		0.25	10
α	45° TP		45° TP		7
1, 2, 10, 12, 13, 14					

NOTE:

- Dimensions are in inches.
- Millimeters are given for general information only.
- Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- Dimension TL measured from maximum HD.
- Body contour optional within zone defined by HD, CD, and Q.
- CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by gauging procedure.
- Dimension LU applies between L1 and L2. Dimension LD applies between L2 and LL minimum. Diameter is uncontrolled in and beyond LL minimum.
- All three leads.
- The collector shall be internally connected to the case.
- Dimension r (radius) applies to both inside corners of tab.
- In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.
- Lead 1 = emitter, lead 2 = base, lead 3 = collector.
- For non-S-suffix devices (TO-5), dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max. For S-suffix types (TO-39), dimension LL = .5 inch (12.70 mm) min. and .750 inch (19.05 mm) max.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Microchip:](#)

[2N5012](#) [2N5011](#) [2N5010](#) [2N5010S](#) [2N5011S](#)